





May 1998

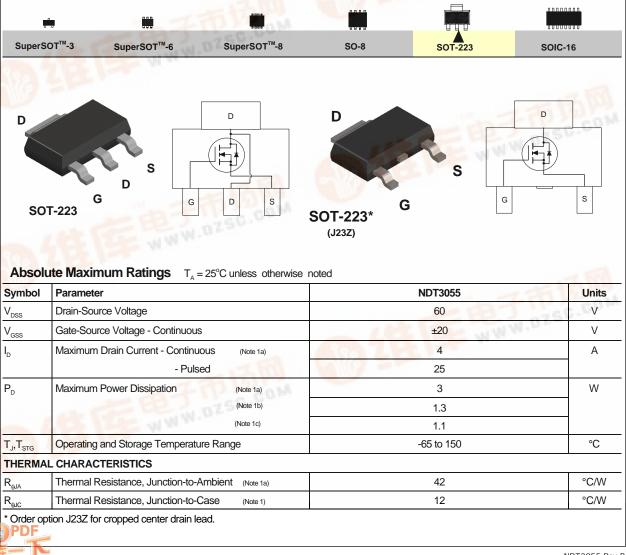
NDT3055 N-Channel Enhancement Mode Field Effect Transistor

General Description

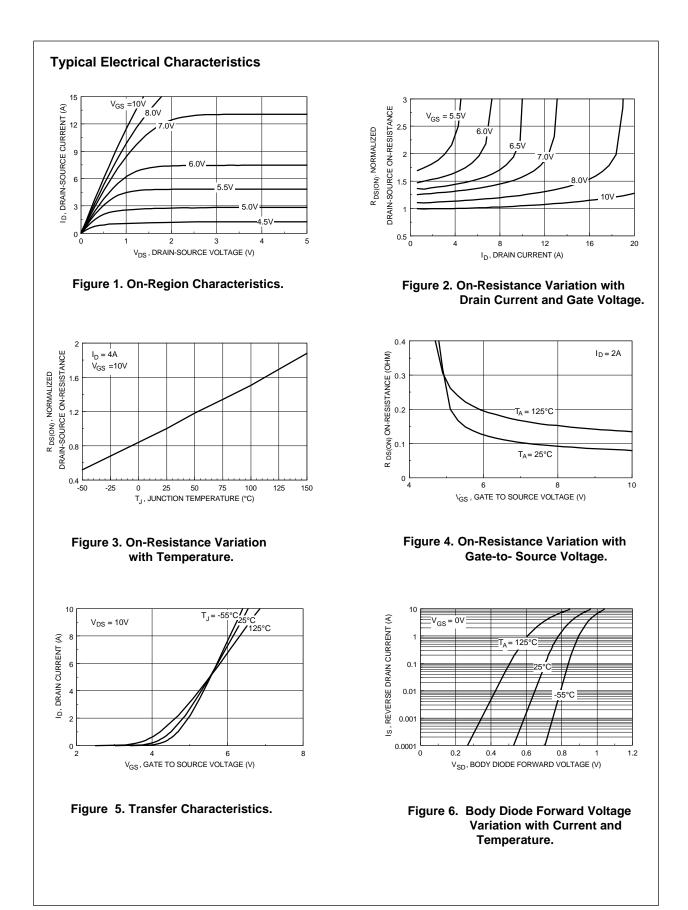
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

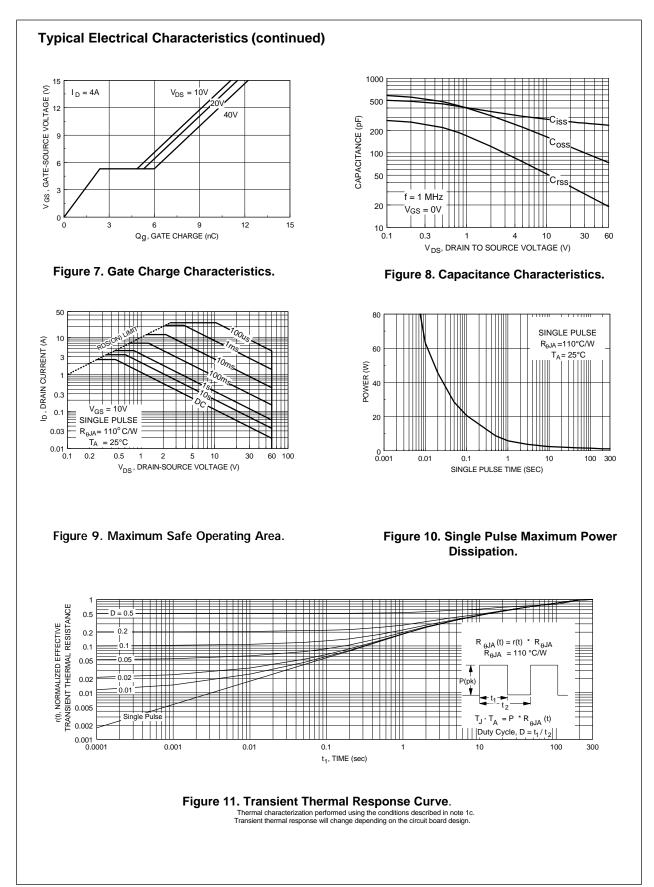
Features

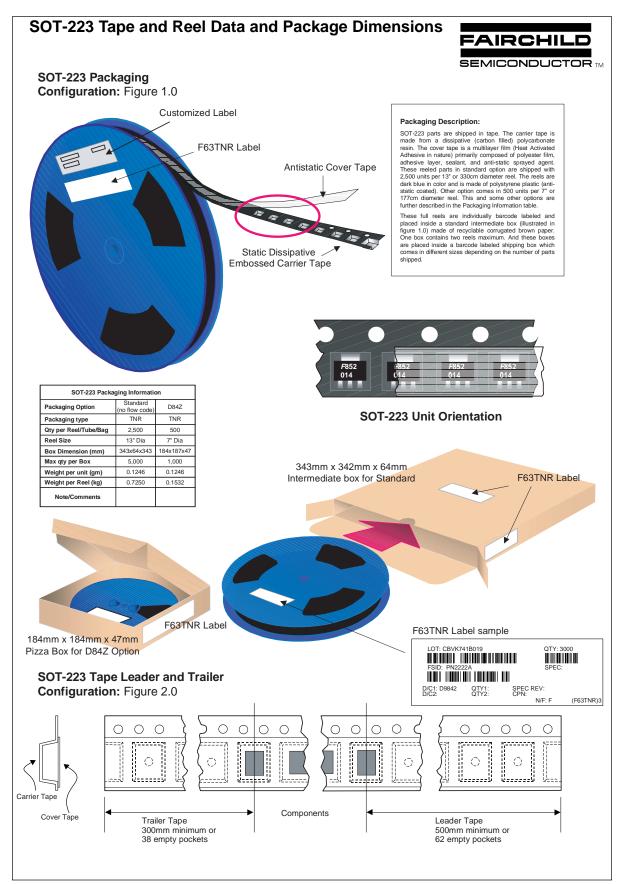
- 4 A, 60 V. $R_{\rm DS(ON)}$ = 0.100 Ω @ V_{GS} = 10 V.
- High density cell design for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.

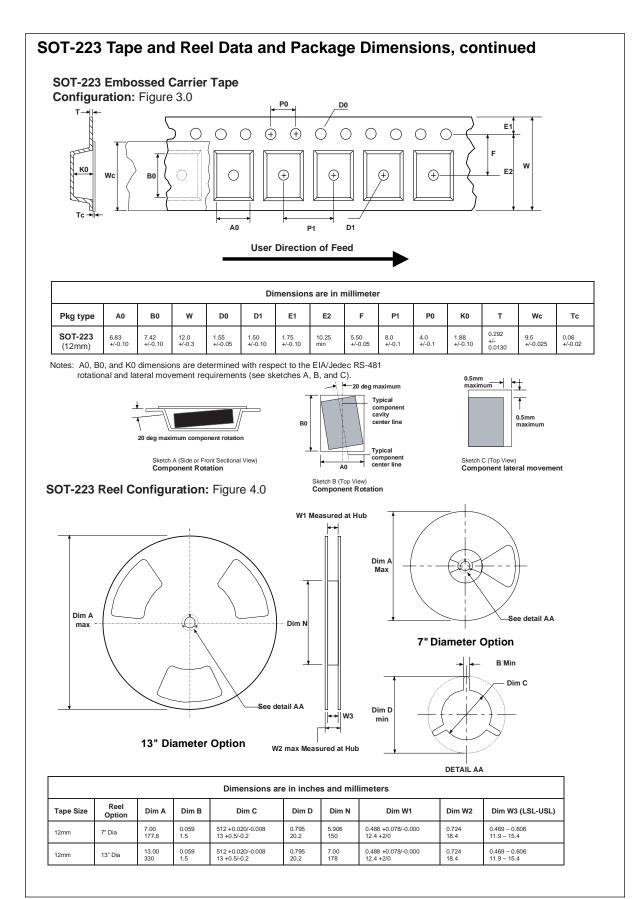


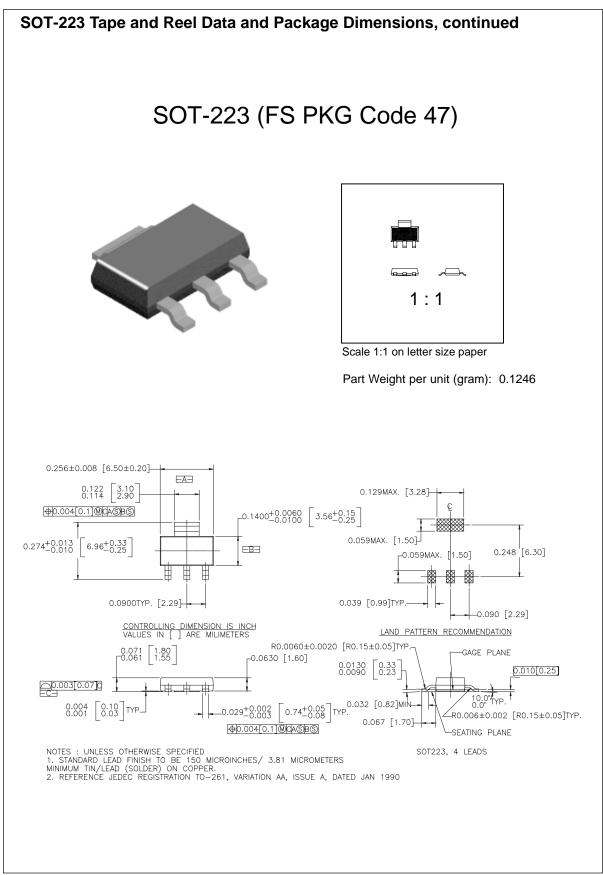
FICS						
urce Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		60			V
wn Voltage Temp. Coefficient	$I_{\rm p}$ = 250 µA, Referenced to 25 °C			63		mV/°C
e Voltage Drain Current	$V_{DS} = 48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$				10	μA
		T_=125°C			100	μA
ody Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
ody Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
CS (Note 2)						
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2	3	4	V
		T _J =125°C	1.5	2.4	3	
ain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 4 \text{ A}$			0.084	0.1	Ω
		T _J =125°C		0.14	0.18	
Drain Current	V _{GS} = 10 V, V _{DS} = 10 V	•	15			А
Transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 4 \text{ A}$			6		S
ERISTICS						
pacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			250		pF
apacitance				100		pF
Transfer Capacitance				30		pF
TERISTICS (Note 2)						
n Delay Time	$V_{DD} = 25 \text{ V}, \ I_{D} = 1.2 \text{ A},$			10	25	ns
n Rise Time	$V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 50 \Omega$			18	50	ns
ff Delay Time				37	65	ns
ff Fall Time				30	60	ns
te Charge	$V_{DS} = 40 \text{ V}, \text{ I}_{D} = 4 \text{ A},$ $V_{GS} = 10 \text{ V}$			9	15	nC
urce Charge				2.3		nC
ain Charge				2.6		nC
E CHARACTERISTICS AND MAX	IMUM RATINGS					
n Continuous Drain-Source Diode Fo	prward Current			2.5	А	
urce Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 2.5 A$ (Note	2)		0.85	1.2	V
h-to-case and case-to-ambient thermal resistance was a stand of the user's board design. ayouts shown below on FR-4 PCB in a still air envir		ed as the solder mor	unting surfa	ce of	the drain p	bins. R _{euc} is
a. 42°C/W when mounted on a 1 in ² pad of 2oz Cu.	b. 95°C/W when mounted pad of 2oz Cu.	dona 0.066 in ²				d on a 0.001;
			a. 42 G/W which modified on a 1 m pad of	2oz Cu. PTP P	202 Cu. Pad of 202 Cu. in ² pad of 202 Cu.	202 Cu. P 무 무 Pad of 202 Cu. in ² pad of 202 Cu. In ² pad of 202 Cu.











TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™
CoolFET™
CROSSVOLT™
E ² CMOS [™]
FACT™
FACT Quiet Series™
FAST®
FASTr™
GTO™
HiSeC™

ISOPLANAR[™] MICROWIRE[™] POP[™] PowerTrench[™] QFET[™] QS[™] Quiet Series[™] SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-8

TinyLogic[™] UHC[™] VCX[™]

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Advance Information	Formative or In Design				
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.			
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.			
Obsolete Not In Production		This datasheet contains specifications on a product that has been discontinued by Fairchild semiconducto The datasheet is printed for reference information only			